

AMENDMENTS TO THE CLAIMS

1. **(Currently Amended)** A thin film-forming sputtering target material having high reflectance, ~~characterized by being~~said material being composed of an Ag base alloy containing 0.0058-1.0 mass% of P.
2. **(Currently Amended)** A thin film-forming sputtering target material having high reflectance, ~~characterized by being~~said material being composed of an Ag base alloy containing 0.0058-1.0 mass% of P and 0.01-2.0 mass% of at least one metallic element selected from In, Sn and Zn.
3. **(Currently Amended)** A thin film-forming sputtering target material having high reflectance, ~~characterized by being~~said material being composed of an Ag base alloy containing 0.0058-1.0 mass% of P, 0.01-0.9 mass% of Au and/or 0.001-5.0 mass% of Pd and/or 0.01-0.9 mass% of Pt.
4. **(Currently Amended)** A thin film-forming sputtering target material having high reflectance, ~~characterized by being~~said material being composed of an Ag base alloy containing 0.0058-1.0 mass% of P and 0.01-5.0 mass% of at least one metallic element selected from Cu, Ni, Fe and Bi.
5. **(Currently Amended)** A thin film-forming sputtering target material having high reflectance, ~~characterized by being~~said material being composed of an Ag base alloy containing 0.0058-1.0 mass% of P, 0.01-2.0 mass% of at least one metallic element selected from In, Sn and Zn, 0.01 to 0.9 mass% of Au and /or 0.01-5.0 mass% of Pd and/or 0.01-0.9 mass% of Pt.

6. (Currently Amended) A thin film-forming sputtering target material having high reflectance, ~~characterized by beingsaid material being~~ composed of an Ag base alloy containing 0.0058-1.0 mass% of P, 0.01-2.0 mass% of at least one metallic element selected from In, Sn and Zn, and 0.01-5.0 mass% of at least one metallic element selected from Cu, Ni, Fe and Bi.

7. (Currently Amended) A thin film-forming sputtering target material having high reflectance, ~~characterized by beingsaid material being~~ composed of an Ag base alloy containing 0.0058-1.0 mass% of P, 0.01-0.9 mass% of Au and/or 0.01-5.0 mass% of Pd and/or 0.01-0.9 mass% of Pt, and 0.01-5.0 mass% of at least one metallic element selected from Cu, Ni, and Bi.

8. (Currently Amended) A thin film-forming sputtering target material having high reflectance, ~~characterized by beingsaid material being~~ composed of an Ag base alloy containing 0.0058-1.0 mass% of P, 0.01-2.0 mass% of at least one metallic element selected from In, Sn and Zn, 0.01-0.9 mass% of Au and/or 0.01-5.0 mass% of Pd and/or 0.01-0.9 mass% of Pt, and 0.01-5.0 mass% of at least one metallic element selected from Cu, Ni, Fe and Bi.

9. (Previously Presented) Thin film formed of an Ag base alloy as set forth in Claim 1.

10. (Previously Presented) Thin film formed of an Ag base alloy as set forth in Claim 2.

11. (Previously Presented) Thin film formed of an Ag base alloy as set forth in Claim 3.

12. (Previously Presented) Thin film formed of an Ag base alloy as set forth in Claim 4.

13. (Previously Presented) Thin film formed of an Ag base alloy as set forth in Claim 5.

14. (Previously Presented) Thin film formed of an Ag base alloy as set forth in Claim 6.

15. (Previously Presented) Thin film formed of an Ag base alloy as set forth in Claim 7.

16. (Previously Presented) Thin film formed of an Ag base alloy as set forth in Claim 8.